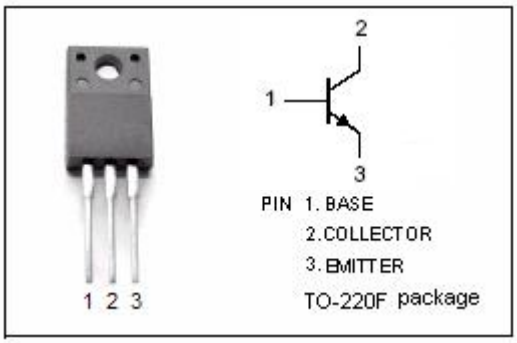
isc Silicon NPN Power Transistor KTD2061

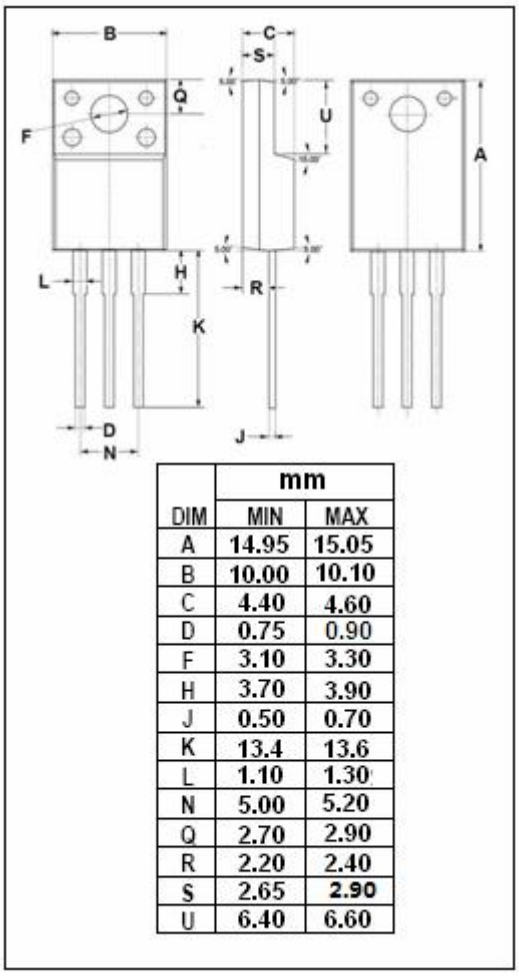
DESCRIPTION

- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 180V(Min)
- Low Collector Saturation Voltage-
  : $V_{CE(sat)}$= 1.0V(Max)@ (I_C= 0.5A, I_B= 50mA)
- Complement to Type KTB1369
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- High Voltage application
- TV, monitor vertical output application
- Driver stage application
- Color TV class B sound output application



DIM	mm MIN	mm MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	200	V
V_{CEO}	Collector-Emitter Voltage	180	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	2	A
I_B	Base Current-Continuous	0.2	A
P_C	Collector Power Dissipation @T_C=25℃	20	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA; I_B= 0	180			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 0.5A; I_B= 50mA			1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 0.5A; V_{CE}= 5V			1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 200V; I_E= 0			1.0	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			1.0	μA
h_{FE}	DC Current Gain	I_C= 0.4A; V_{CE}= 10V	70		240	
f_T	Current-Gain—Bandwidth Product	I_C= 0.4A; V_{CE}= 10V		100		MHz

◆ **h_{FE} Classification**

O	Y
70-140	120-240